

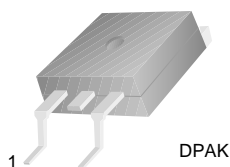


FJD3305H1

NPN Silicon Transistor

High Voltage Switch Mode Application

- Fast Speed Switching
- Wide Safe Operating Area
- Suitable for Electronic Ballast Application



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings * $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|---|-----------|------------------|
| V_{CBO} | Collector-Base Voltage | 700 | V |
| V_{CEO} | Collector-Emitter Voltage | 400 | V |
| V_{EBO} | Emitter-Base Voltage | 9 | V |
| I_C | Collector Current (DC) | 4 | A |
| I_{CP} | Collector Current (Pulse) | 8 | A |
| I_B | Base Current | 2 | A |
| P_C | Collector Dissipation, $T_a = 25^\circ\text{C}$ | 1.1 | W |
| | $T_C = 25^\circ\text{C}$ | 50 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | -65 ~ 150 | $^\circ\text{C}$ |

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------|---|-------|---------------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 110 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 2.0 | $^\circ\text{C}/\text{W}$ |

* Device mounted on minimum pad size

Ordering Information

| Part Number | Marking | Package | Packing Method | Remarks |
|-------------|---------|---------|----------------|---------|
| FJD3305H1TM | J3305H1 | D-PAK | Tape & Reel | |

Electrical Characteristics * $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Conditions | Min. | Typ. | Max | Units |
|---------------|--------------------------------------|---|------|------|-----|---------------|
| BV_{CBO} | Collector-Base Breakdwon Voltage | $I_C = 500\mu\text{A}, I_E = 0$ | 700 | | | V |
| BV_{CEO} | Collector-Emitter Breakdown Voltage | $I_C = 5\text{mA}, I_B = 0$ | 400 | | | V |
| BV_{EBO} | Emitter-Base Breakdown Voltage | $I_E = 500\mu\text{A}, I_C = 0$ | 9 | | | V |
| I_{CBO} | Collector Cut-off Current | $V_{CB} = 700\text{V}, I_E = 0$ | | | 1 | μA |
| I_{EBO} | Emitter Cut-off Current | $V_{EB} = 9\text{V}, I_C = 0$ | | | 1 | μA |
| h_{FE1} | DC Current Gain * | $V_{CE} = 5\text{V}, I_C = 1\text{A}$ | 19 | | 28 | |
| h_{FE2} | | $V_{CE} = 5\text{V}, I_C = 2\text{A}$ | 8 | | 40 | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 1\text{A}, I_B = 0.2\text{A}$ | | | 0.5 | V |
| | | $I_C = 2\text{A}, I_B = 0.5\text{A}$ | | | 0.6 | V |
| | | $I_C = 4\text{A}, I_B = 1\text{A}$ | | | 1.0 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C = 1\text{A}, I_B = 0.2\text{A}$ | | | 1.2 | V |
| | | $I_C = 2\text{A}, I_B = 0.5\text{A}$ | | | 1.6 | V |
| f_T | Current Gain Bandwidth Product | $V_{CE} = 10\text{V}, I_C = 0.5\text{A}$ | 4 | | | MHz |
| C_{ob} | Output Capacitance | $V_{CB} = 10\text{V}, f = 1\text{MHz}$ | | 65 | | pF |
| t_{ON} | Turn On Time | $V_{CC} = 125\text{V}, I_C = 2\text{A}$ $I_{B1} = -I_{B2} = 0.4\text{A}$ $R_L = 62.5\Omega$ | | | 0.8 | μs |
| t_{STG} | Storage Time | | | | 4.0 | μs |
| t_F | Fall Time | | | | 0.9 | μs |

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

Figure 1. Static Characteristic

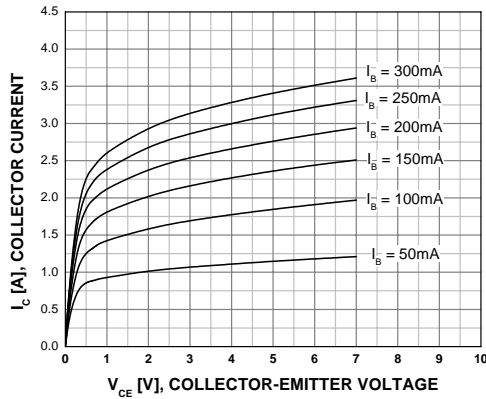


Figure 2. DC Current Gain

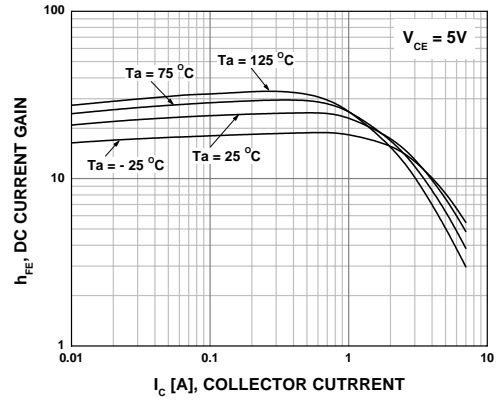


Figure 3. Collector- Emitter Saturation Voltage

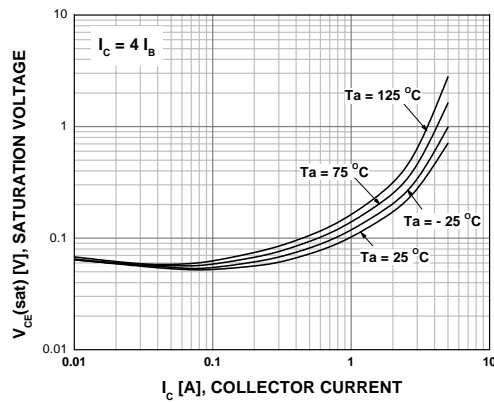


Figure 4. Base - Emitter Saturation Voltage

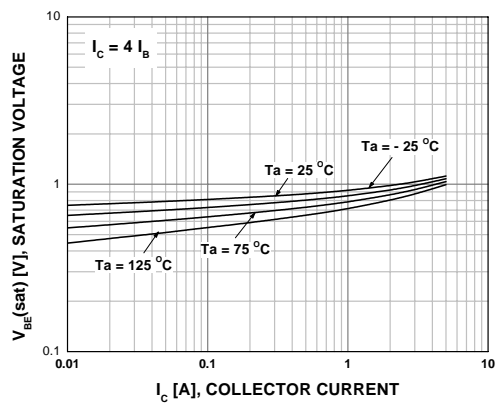


Figure 5. Switching Time

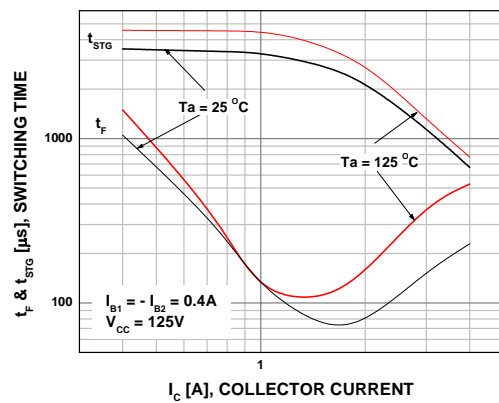
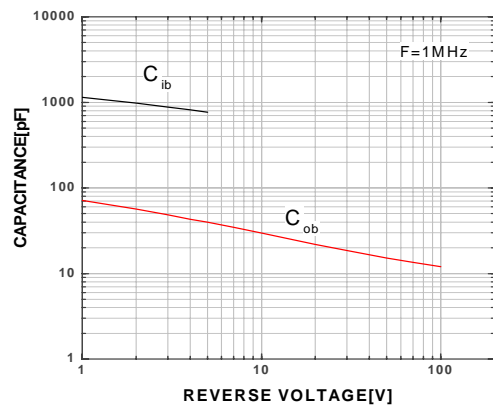


Figure 6. Capacitance



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Figure 7. Reverse Biased Safe Operating Area

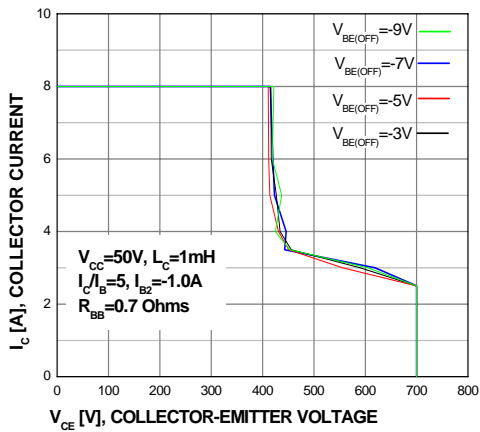


Figure 8. RBSOA Collector- Emitter Saturation Voltage

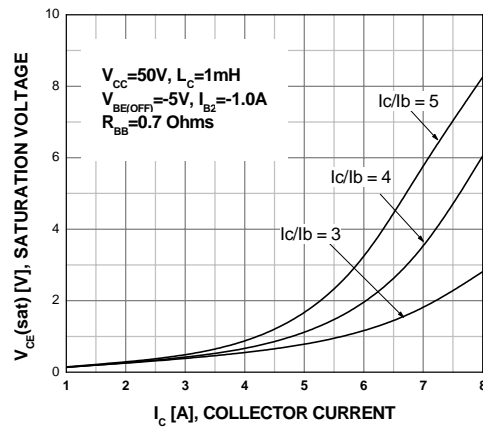


Figure 9. RBSOA Turn-on Pulse Width vs Collector Current

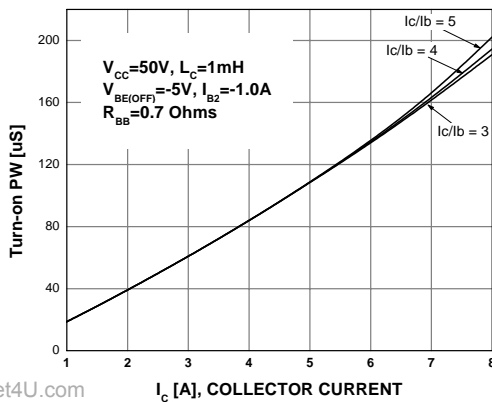


Figure 10. Power Derating

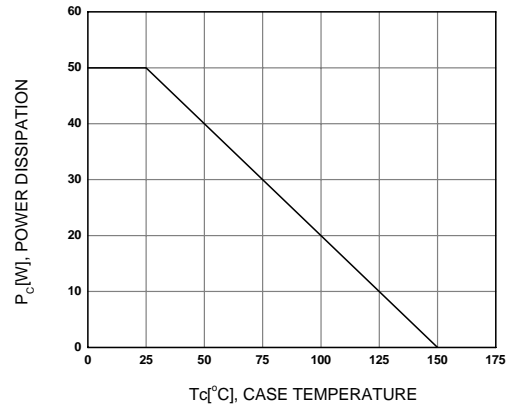
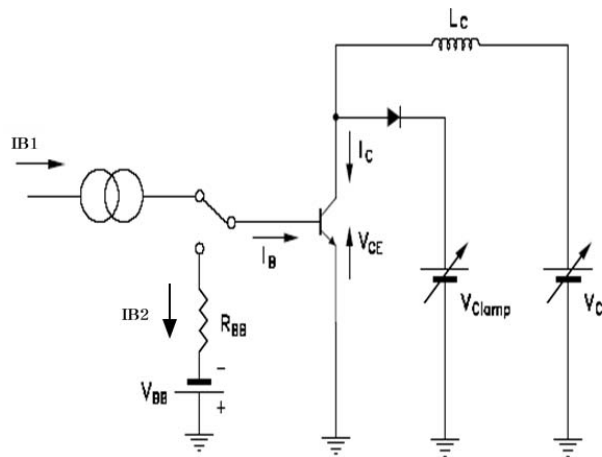


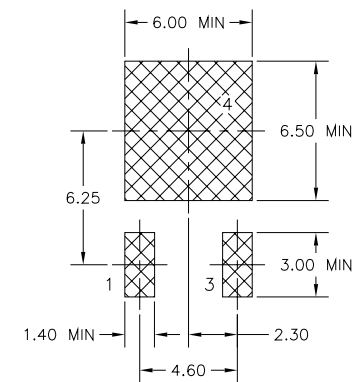
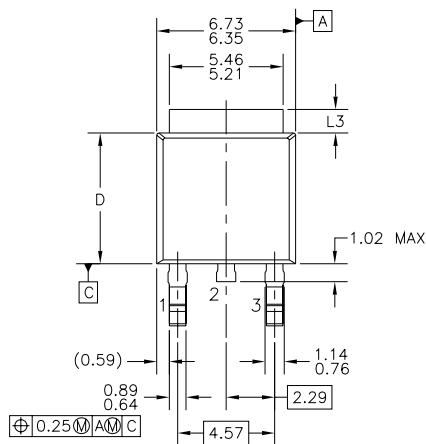
Figure 11. RBSOA Test Circuit



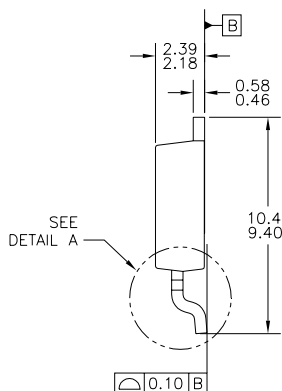
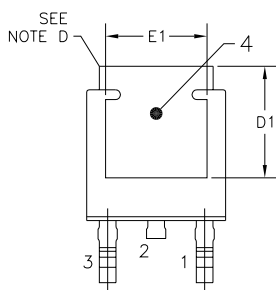
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Mechanical Dimensions

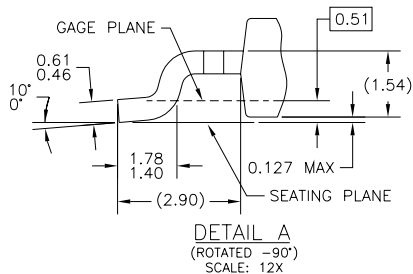
D-PAK



LAND PATTERN RECOMMENDATION



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NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
 - B) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA & AB, DATED NOV. 1999.
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
 - D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
 - E) DIMENSIONS L3,D,E1&D1 TABLE:
- | | OPTION AA | OPTION AB |
|----|-----------|-----------|
| L3 | 0.89-1.27 | 1.52-2.03 |
| D | 5.97-6.22 | 5.33-5.59 |
| E1 | 4.32 MIN | 3.81 MIN |
| D1 | 5.21 MIN | 4.57 MIN |
- F) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.

Dimensions in Millimeters





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